
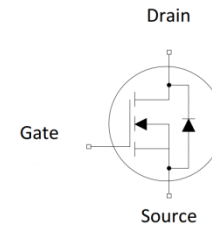
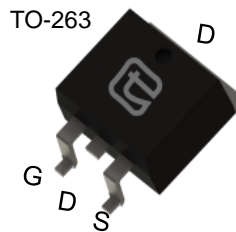




# 80V N-Channel Trench MOSFET

<p><b>Features</b></p> <ul style="list-style-type: none"> <li>● Trench Power Technology</li> <li>● Low <math>R_{DS(ON)}</math></li> <li>● Low Gate Charge</li> <li>● Optimized for Fast-switching Applications</li> </ul> <p><b>Applications</b></p> <ul style="list-style-type: none"> <li>● Synchronous Rectification in DC/DC and AC/DC Converters</li> <li>● Isolated DC/DC Converters in Telecom and Industrial</li> </ul>	<p><b>Product Summary</b></p> <p><math>V_{DS}</math> 80V</p> <p><math>R_{DS(ON)}</math> (at <math>V_{GS}=10V</math>) &lt; 6m<math>\Omega</math></p> <p><math>I_D</math> (at <math>V_{GS}=10V</math>) 120A</p> <p>100% UIS Tested</p> 
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Device	Package	Marking
TMB120N08A	TO-263	120N08A
TMP120N08A	TO-220	120N08A

## Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ , unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage ( $V_{GS} = 0V$ )	$V_{DSS}$	80	V
Continuous Drain Current	$I_D$	$T_C = 25^\circ\text{C}$	120
		$T_C = 100^\circ\text{C}$	84
Pulsed Drain Current (note1)	$I_{DM}$	480	A
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	V
Single Pulse Avalanche Energy (note2)	$E_{AS}$	540	mJ
Avalanche Current	$I_{AS}$	60	A
Power Dissipation (note3)	$P_D$	$T_C = 25^\circ\text{C}$	208
		$T_C = 100^\circ\text{C}$	104
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55~+175	$^\circ\text{C}$

## Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{thJC}$	0.72	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient	$R_{thJA}$	62.5	



Specifications $T_J = 25^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	80	--	--	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 80V, V_{GS} = 0V, T_J = 25^\circ\text{C}$	--	--	1	$\mu A$
		$V_{DS} = 80V, V_{GS} = 0V, T_J = 100^\circ\text{C}$	--	--	25	
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 20V$	--	--	$\pm 100$	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.0	--	4.0	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 30A$	--	4.6	6.0	m $\Omega$
Forward Transconductance	$g_{fs}$	$V_{DS} = 5V, I_D = 20A$	40	--	--	S
<b>Dynamic</b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0V,$ $V_{DS} = 40V,$ $f = 1.0\text{MHz}$	--	5400	--	pF
Output Capacitance	$C_{oss}$		--	390	--	
Reverse Transfer Capacitance	$C_{rss}$		--	260	--	
Total Gate Charge	$Q_g$	$V_{DD} = 40V, I_D = 20A,$ $V_{GS} = 10V$	--	130	--	nC
Gate-Source Charge	$Q_{gs}$		--	24	--	
Gate-Drain Charge	$Q_{gd}$		--	49	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 40V, I_D = 2A,$ $R_G = 2.5\Omega$	--	28	--	ns
Turn-on Rise Time	$t_r$		--	29.5	--	
Turn-off Delay Time	$t_{d(off)}$		--	41	--	
Turn-off Fall Time	$t_f$		--	15.6	--	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Body Diode Current	$I_S$	$T_C = 25^\circ\text{C}$	--	--	120	A
Pulsed Diode Forward Current	$I_{SM}$		--	--	480	
Body Diode Voltage	$V_{SD}$	$T_J = 25^\circ\text{C}, I_{SD} = 20A, V_{GS} = 0V$	--	--	1.2	V
Reverse Recovery Time	$t_{rr}$	$I_F = 20A,$ $di_F/dt = 500A/\mu s$	--	45	--	ns
Reverse Recovery Charge	$Q_{rr}$		--	54	--	nC

**Notes**

1. Repetitive Rating: Pulse Width limited by maximum junction temperature
2.  $I_{AS} = 60A, V_{DD} = 50V, R_G = 25\Omega$ , Starting  $T_J = 25^\circ\text{C}$
3. The power dissipation PD is based on  $TJ(MAX)=175^\circ\text{C}$ , using junction-to-case thermal resistance.



Typical Characteristics  $T_J = 25^\circ\text{C}$ , unless otherwise noted

Figure 1. Output Characteristics

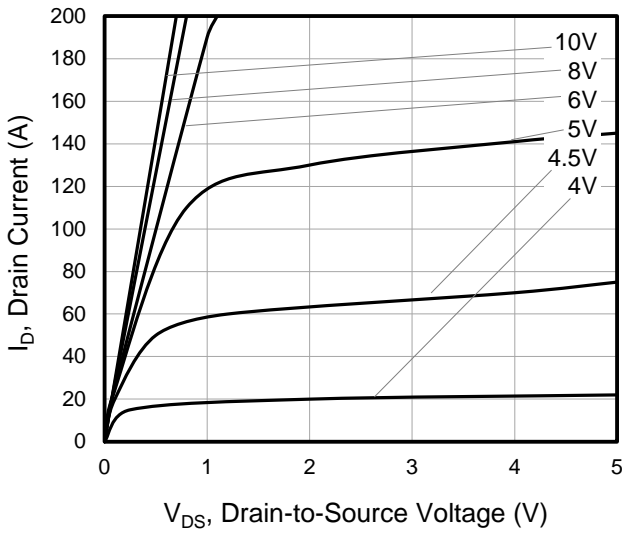


Figure 2. Transfer Characteristics

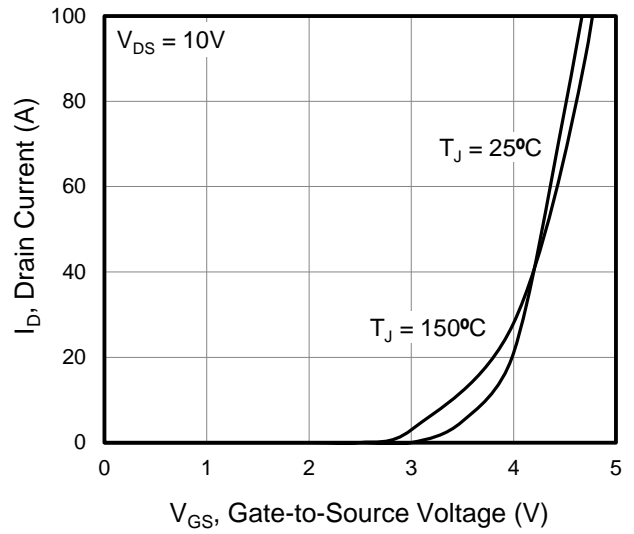


Figure 3. On-Resistance vs. Drain Current

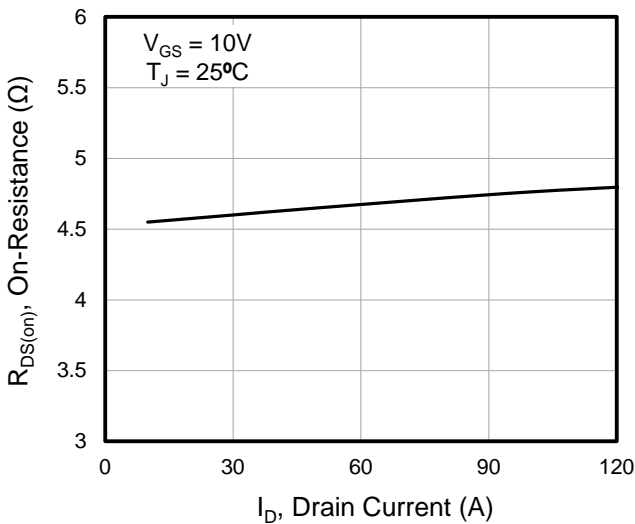


Figure 4. Capacitance

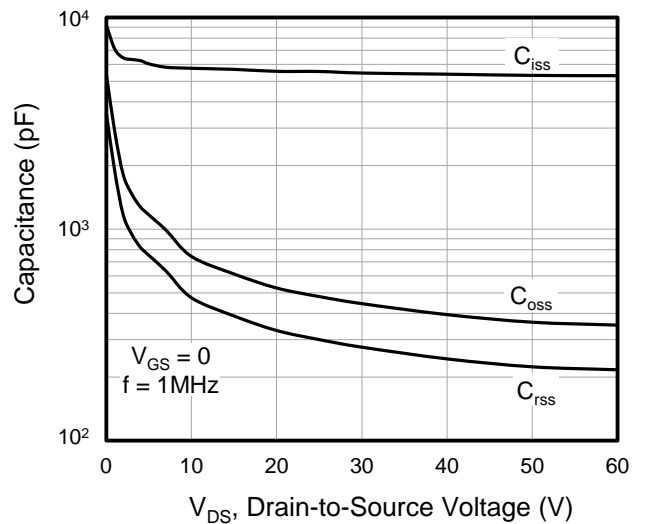


Figure 5. Gate Charge

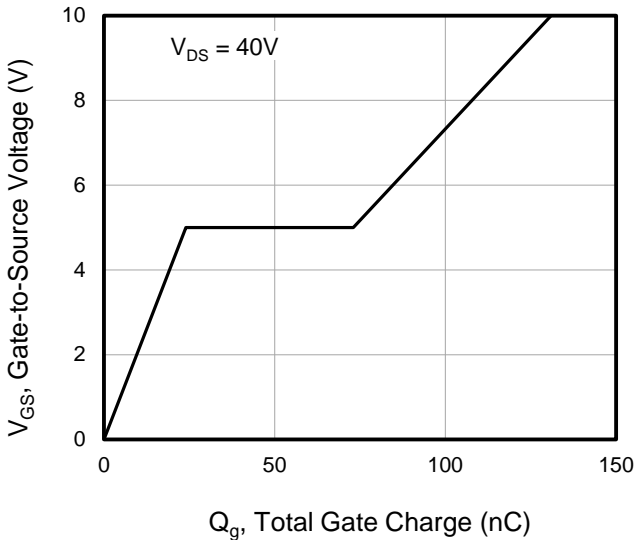
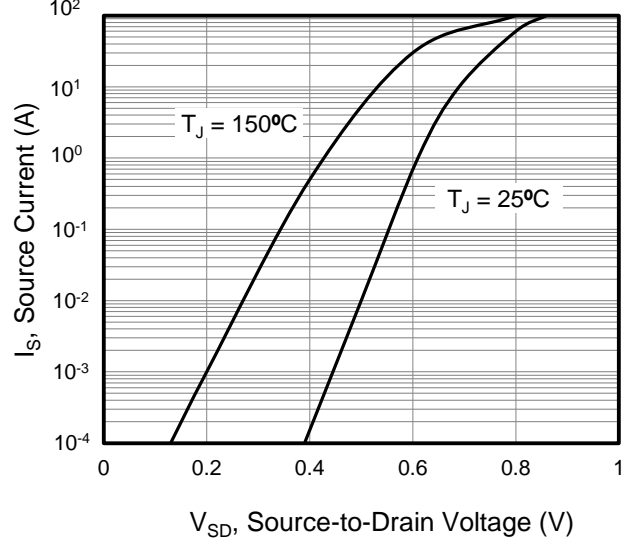


Figure 6. Body Diode Forward Voltage





Typical Characteristics  $T_J = 25^\circ\text{C}$ , unless otherwise noted

Figure 7. On-Resistance vs. Temperature

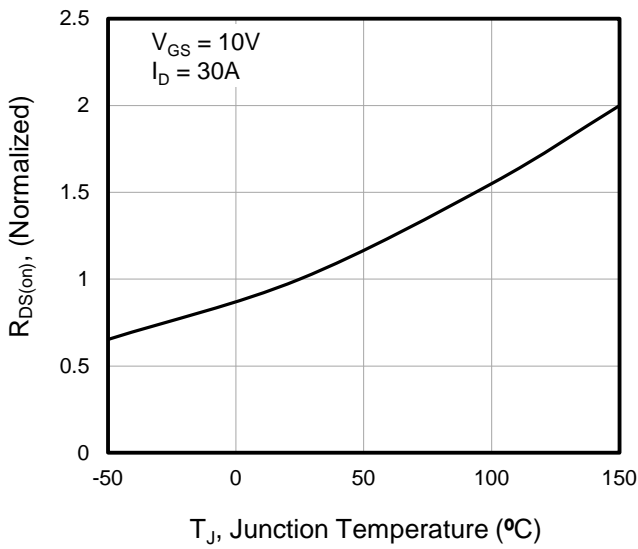


Figure 8. Threshold Voltage vs. Temperature

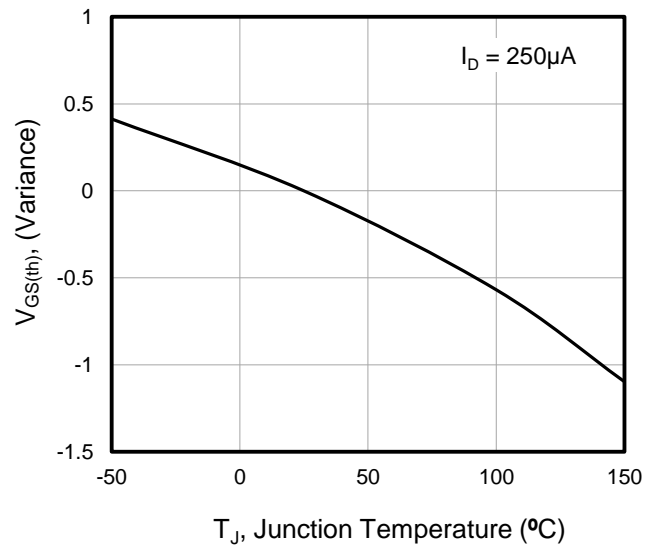


Figure 9. Transient Thermal Impedance

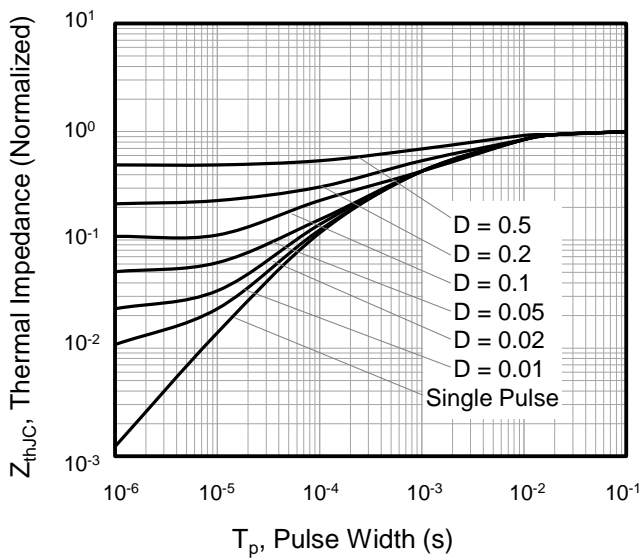


Figure 10. Safe operation area

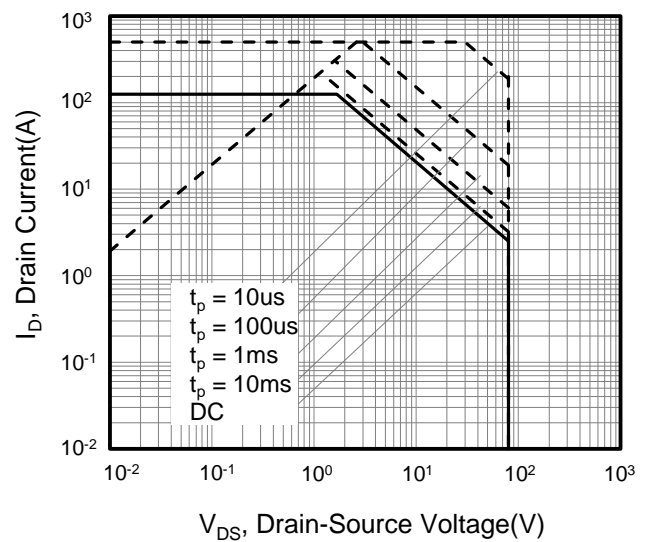




Figure A: Gate Charge Test Circuit and Waveform

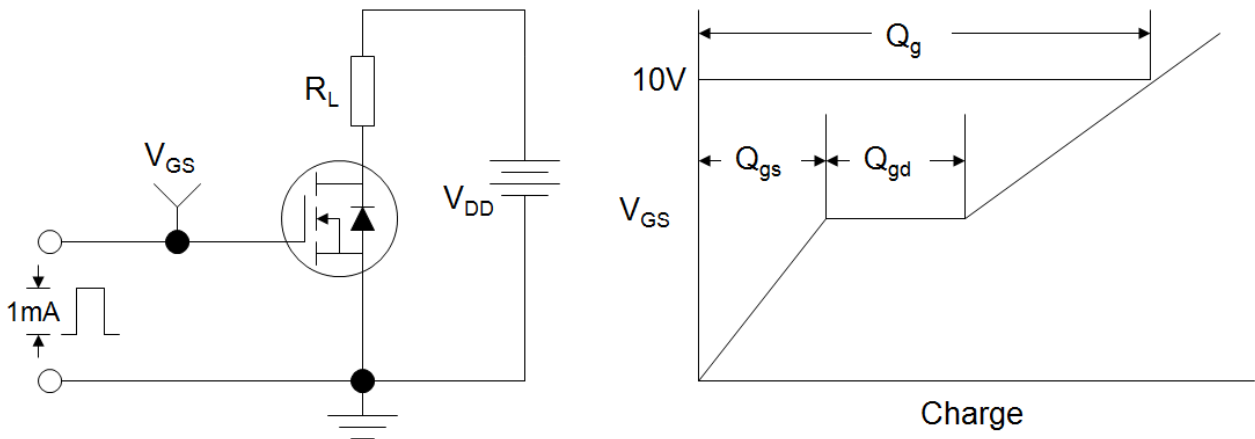


Figure B: Resistive Switching Test Circuit and Waveform

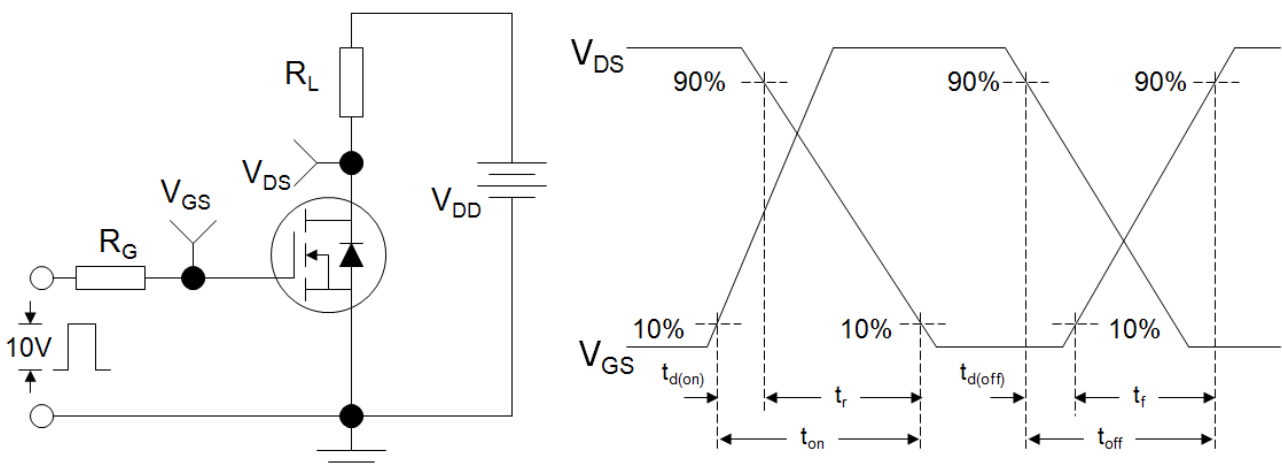
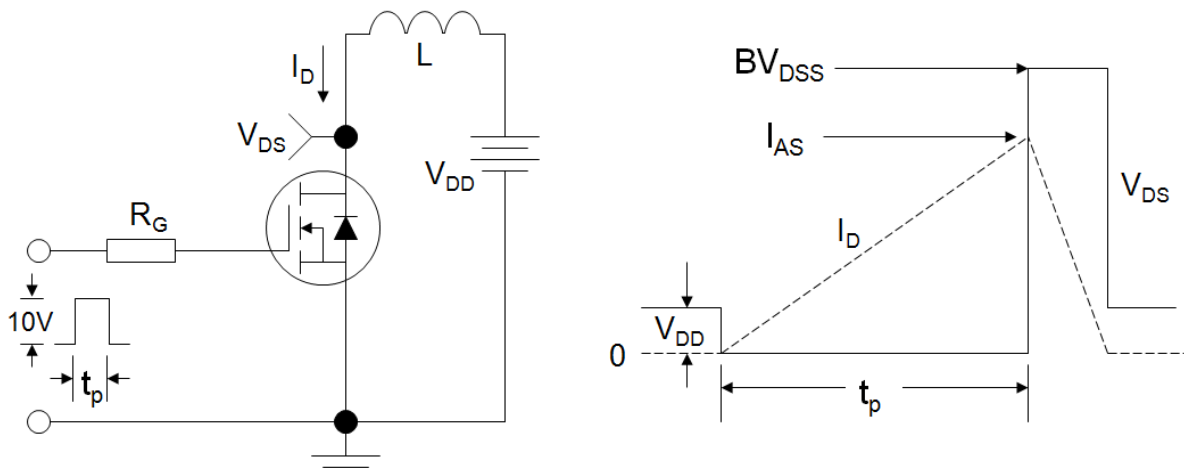
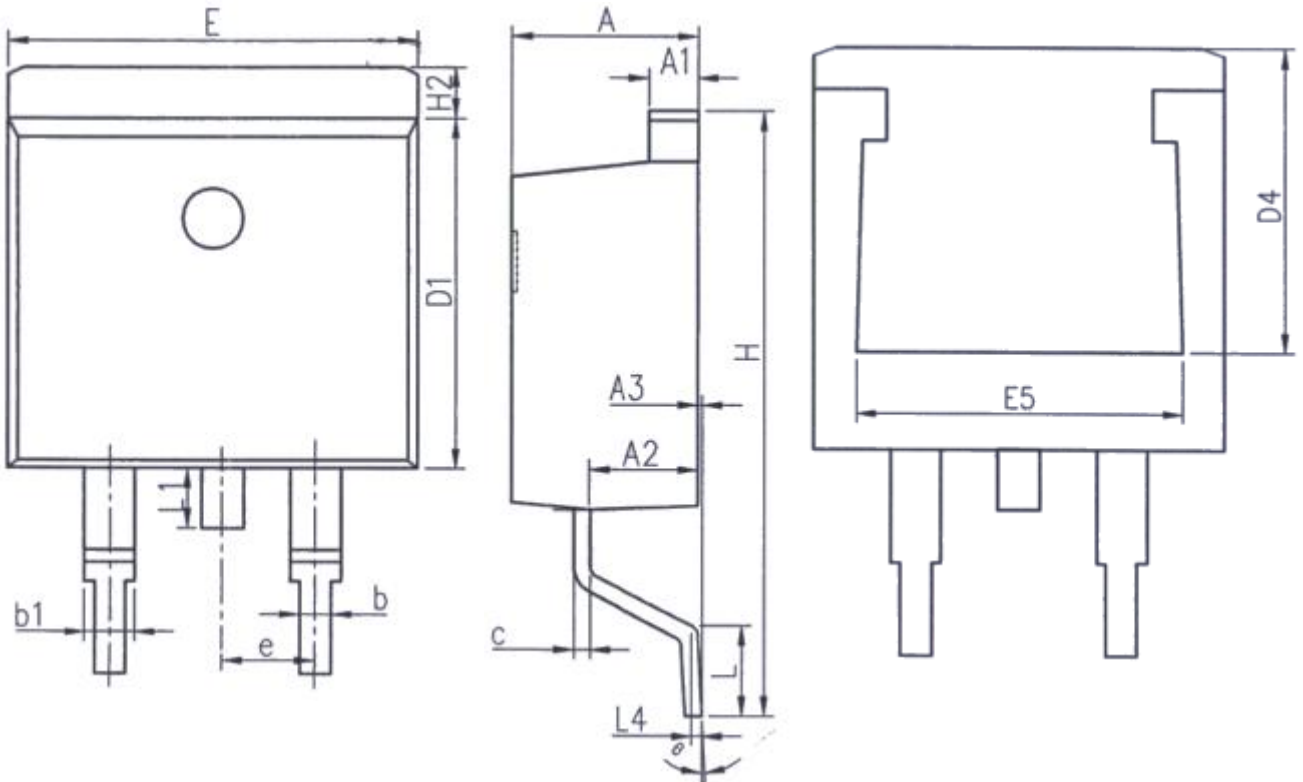


Figure C: Unclamped Inductive Switching Test Circuit and Waveform





### TO-263

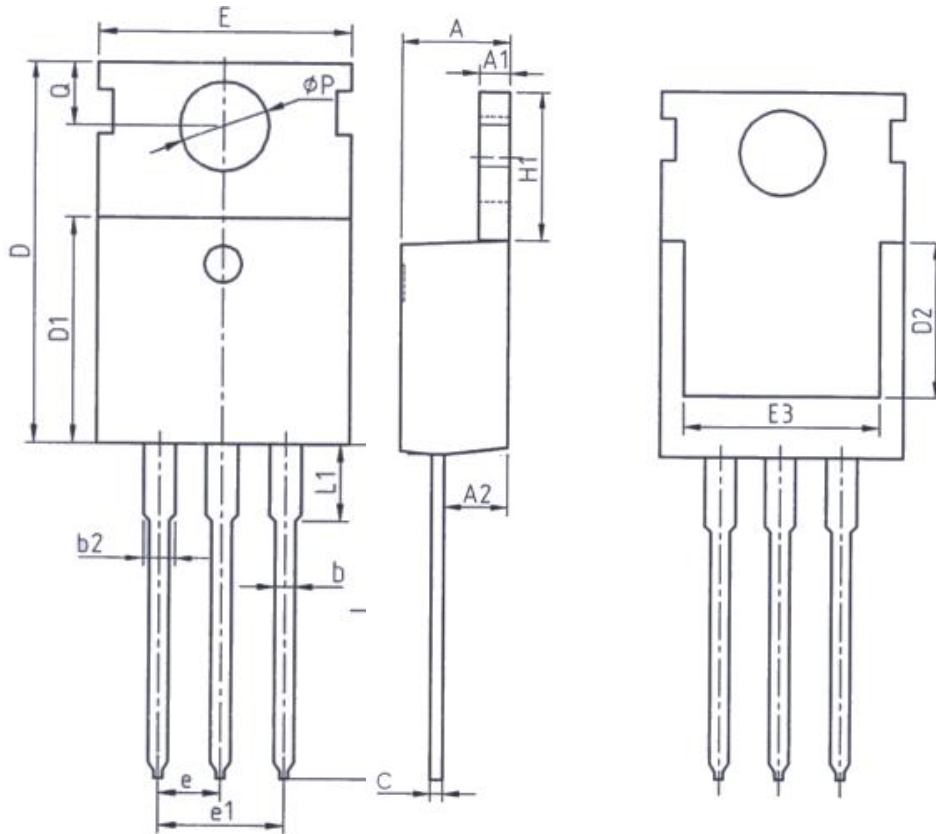


Unit: mm		
Symbol	Min.	Max.
A	4.37	4.77
A1	1.22	1.42
A2	2.49	2.89
A3	0.00	0.25
b	0.70	0.96
b1	1.17	1.47
c	0.30	0.53
D1	8.50	8.90
D4	6.60	-

Unit: mm		
Symbol	Min.	Max.
E	9.86	10.36
E5	7.06	-
e	2.54BSC	
H	14.70	15.50
L	2.00	2.60
L1	1.40	1.70
L4	0.25BSC	
θ	0°	9°



### TO-220



Unit: mm		
Symbol	Min.	Max.
A	4.37	4.77
A1	1.25	1.45
A2	2.20	2.60
b	0.70	0.95
b2	1.17	1.47
c	0.40	0.65
D	15.10	16.10
D1	8.80	9.40
D2	5.50	-

Unit: mm		
Symbol	Min.	Max.
E	9.70	10.30
E3	7.00	-
e	2.54BSC	
e1	5.08BSC	
H1	6.25	6.85
L	12.75	13.80
L1	-	3.40
P	3.40	3.80
Q	2.60	3.00



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